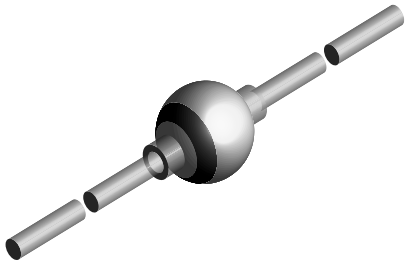
Standard Sinterglass Diode

Features

- High temperature metallurgically bonded constructed rectifiers
- Cavity-free glass passivated junction
- Hermetically sealed package
- 3.0 ampere operation at T_{amb}= 70 °C with no thermal runaway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Mechanical Data

Case: Sintered glass case, G-3

Terminals: Solder plated axial leads, solderable per MIL-STD-750, Method 2026

Polarity: Color band denotes cathode end

Mounting Position: Any

Weight: approx. 1100 mg

Parts Table

Part	Type differentiation	Package
G3A	V_{RRM} = 50 V	G-3
G3B	V_{RRM} = 100 V	G-3
G3D	V_{RRM} = 200 V	G-3
G3G	V_{RRM} = 400 V	G-3
G3J	V_{RRM} = 600 V	G-3
G3K	V_{RRM} = 800 V	G-3
G3M	V_{RRM} = 1000 V	G-3

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Part	Symbol	Value	Unit
Reverse voltage = Repetitive peak reverse voltage	see electrical characteristics	G3A	$V_R = V_{RRM}$	50	V
		G3B	$V_R = V_{RRM}$	100	V
		G3D	$V_R = V_{RRM}$	200	V
		G3G	$V_R = V_{RRM}$	400	V
		G3J	$V_R = V_{RRM}$	600	V
		G3K	$V_R = V_{RRM}$	800	V
		G3M	$V_R = V_{RRM}$	1000	V
Maximum average forward rectified current	0.375 " (9.5 mm) lead length at T_{amb} = 70 °C		$I_{F(AV)}$	3.0	A

Parameter	Test condition	Part	Symbol	Value	Unit
Peak forward surge current	8.3 ms single half sine-wave superimposed on rated load (JEDEC Method)		I_{FSM}	125	A
Maximum full load reverse current	full cycle average 0.375 " (9.5 mm) lead length at T_{amb} = 70 °C		$I_{R(AV)}$	200	µA
Operating junction and storage temperature range			T_J, T_{STG}	- 55 to + 175	°C

Maximum Thermal Resistance

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Typical thermal resistance [1]		$R_{\theta JA}$	20	K/W
		$R_{\theta JL}$	10	K/W

[1] Thermal resistance from junction to ambient and from junction to lead at 0.375 " (9.5 mm) lead length, with both leads mounted between heatsinks

Electrical Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Maximum instantaneous forward voltage	I_F = 3 A	V_F			1.2	V
		V_F			1.2	V
		V_F			1.1	V
		V_F			1.1	V
		V_F			1.1	V
		V_F			1.1	V
		V_F			1.1	V
Maximum reverse current	$V_R = V_{RRM}$, T_{amb} = 25 °C	I_R			5.0	µA
	$V_R = V_{RRM}$, T_{amb} = 150 °C	I_R			100	µA
Typical reverse recovery time	I_F = 0.5 A, I_R = 1.0 A, I_{rr} = 0.25 A	t_{rr}		3.0		µs
Typical junction capacitance	V_R = 4.0 V, f = 1 MHz	C_j		40		pF

Typical Characteristics (T_{amb} = 25 °C unless otherwise specified)

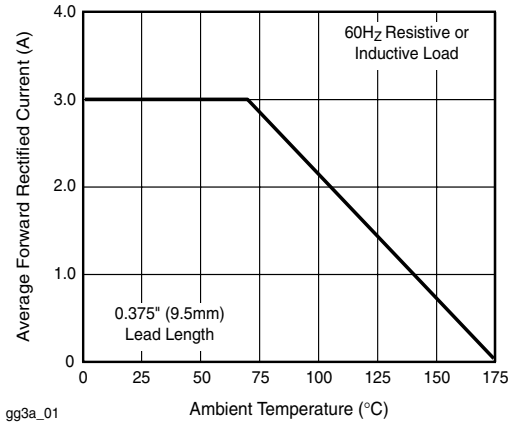


Figure 1. Forward Current Derating Curve

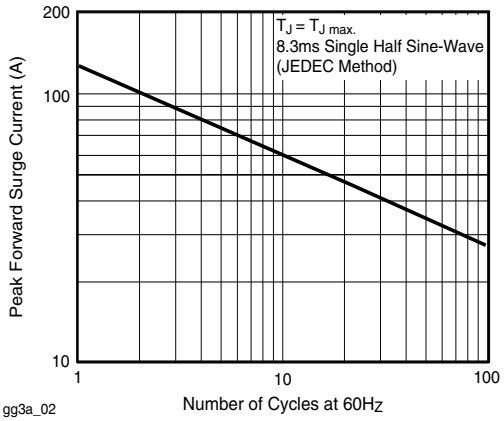


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current

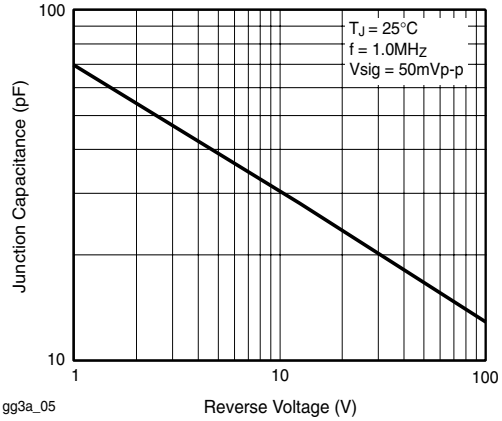


Figure 5. Typical Junction Capacitance

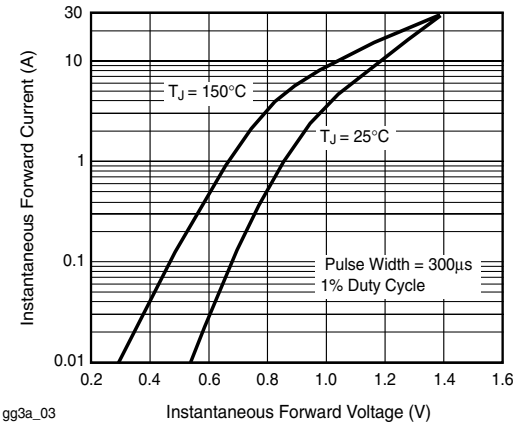


Figure 3. Typical Instantaneous Forward Characteristics

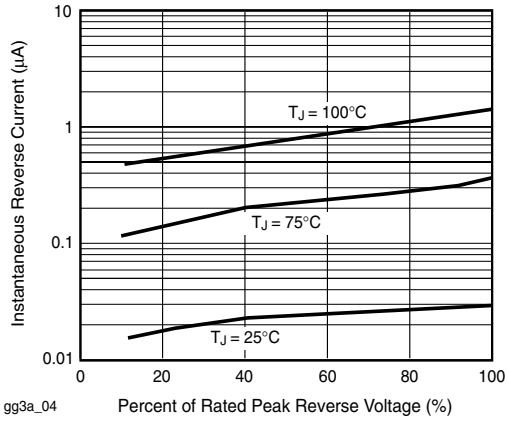
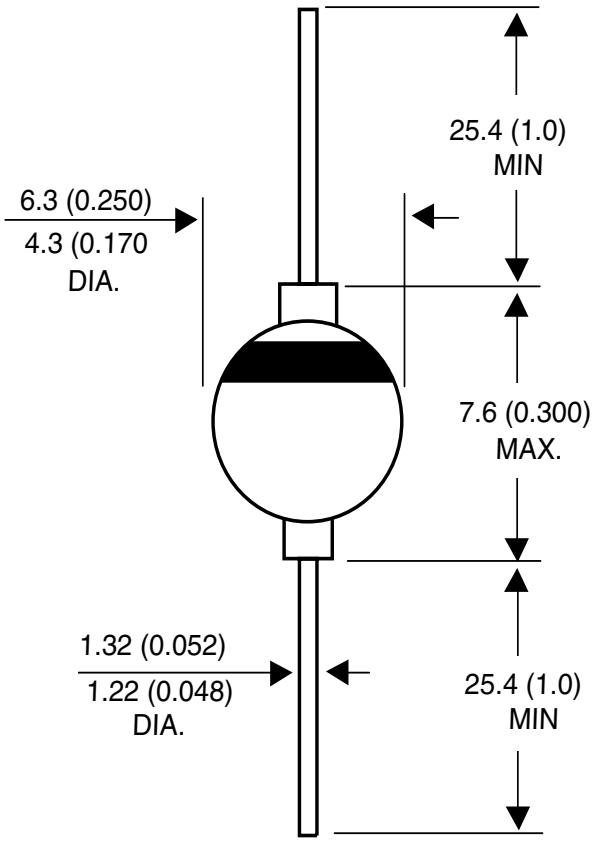


Figure 4. Typical Reverse Characteristics

Package Dimensions in mm (Inches)



Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operatingsystems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany
Telephone: 49 (0)7131 67 2831, Fax number: 49 (0)7131 67 2423

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